

MPFF400R12KBF

1200V 400A IGBT Module

Electrical Features

- Trench/Fieldstop IGBT
- Half-bridge
- Standard package
- High short circuit capability
- Including anti-parallel FWD



Typical Applications

- Frequency converter
- UPS
- High Power Converters
- Motor Drives
- Wind Turbines

IGBT, Inverter

Maximu	m Rated Values						
Symbol	Item	Conditions			Rating		Unit
IGBT							
V_{CES}	Collector-emitter voltage	T _{vj} =25°C			1200		V
V_{GES}	Gate-emitter voltage	-	-			±20	
$I_{\rm C}$	Collector current,DC	$T_{C}=100^{\circ}\text{C}, T_{vj}=175^{\circ}$	T _C =100°C,T _{vj} =175°C			400	
I_{CRM}	Repetitive peak collector current	t _p =1ms			80	00	A
t_{SC}	Short circuit withstand time	V _{GE} =15V, V _{CC} =600V, T _{vj} ≤150°C			1	0	μs
P _{tot}	Total power dissipation	$T_{\rm C}$ =25°C, $T_{\rm vj}$ =175°C			24	19	W
Characte	eristics Values						
Symbol	Item	Conditions			Values		Unit
IGBT				Min.	Typ.	Max.	
I _{CES}	Collector-emitter cut-off current	V _{CE} =1200V,V _{GE} =0V,T _{vj} =25°C		-	-	1	mA
I _{GES}	Gate leakage current	V _{CE} =0V,V _{GE} =20V,T _{vj} =25°C		-	-	250	nA
$V_{\text{GE(th)}}$	Gate-emitter threshold voltage	$I_C=16\text{mA}, V_{CE}=V_{GE}, T_{vj}=25^{\circ}\text{C}$		5.2	5.7	6.4	
	Collector-emitter saturation voltage	I _C =400A V _{GE} =15V	T _{vj} =25°C	-	1.65	ı	V
V _{CEsat}			T _{vj} =125°C	-	1.90	ı	V
			T _{vj} =150°C	-	1.93	ı	
Cies	Input capacitance	$V_{CE}=25V,V_{GE}=0V$		-	43.6	ı	nF
C _{res}	Reverse transfer capacitance	f=1MHz,T _{vj} =25°C		-	1.4	-	ШГ
Q_{G}	Gate charge	V _{CC} =600V, I _C =400A, V _{GE} =15V		-	4.1	-	uС
$R_{\rm g}$	Internal gate resistance	T _{vj} =25°C		-	0.43	-	Ω

			T _{vj} =25°C	-	166	-	
$t_{d(on)}$	Turn-on delay time		$T_{vj}=125$ °C	-	156	-	
			T _{vi} =150°C	-	155	-	
			T _{vj} =25°C	-	163	-	
t_r	Rise time	$V_{CC}=600V$,	T _{vj} =125°C	-	163	-	
		I _C =400A,	T _{vj} =150°C	-	169	-	
		$V_{GE}=\pm 15V$,	T _{vj} =25°C	-	833	-	ns
$t_{d(off)} \\$	Turn-off delay time	$R_{G(on)}=5.1 \Omega$,	T _{vj} =125°C	-	924	-	
		$R_{G(off)}=5.1 \Omega$,	T _{vj} =150°C	-	931	-	
		L _{load} =100uH	T _{vj} =25°C	-	134	ı	
t_{f}	Fall time	di/dt=5390A/μs	$T_{vj}=125$ °C	-	270	1	
		(T _{vj} =150°C)	T _{vj} =150°C	-	296	-	
		du/dt=2546V/μs	T _{vj} =25°C	-	67.7	-	
E_{on}	Turn-on energy (per pulse)	(T _{vj} =150°C)	T _{vj} =125°C	-	86.3	-	
			T _{vj} =150°C	-	93.3	-	т
			T _{vj} =25°C	-	52.5	-	mJ
$E_{\rm off}$	Turn-off energy (per pulse)		T _{vj} =125°C	-	64.8	1	1
			T _{vj} =150°C	-	67.4	-	
R _{thJC}	Thermal resistance, junction to case	per IGBT	1 3	-	0.062	-	K/W
till C	771 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	per IGBT/ λgrease=1W/(m·K) -			-	K/W	
R _{thCH}	Thermalresistance, case to heatsink	per 10b1/ Agrease					
	Thermalresistance, case to heatsink Temperature under switching conditions	per IOB1/ Agrease		-40		150	°C
R_{thCH}	Temperature under switching conditions	per IGB1/ Agrease	, ,	-40		150	°C
R_{thCH} T_{vjop} Diode, 1	Temperature under switching conditions			-40		150	℃
R _{thCH} T _{vjop} Diode, I Maximus Symbol	Temperature under switching conditions Inverter m Rated Values Item		nditions	-40	Rat		°C Unit
R _{thCH} T _{vjop} Diode, I Maximu	Temperature under switching conditions Inverter m Rated Values			-40	1		
R _{thCH} T _{vjop} Diode, I Maximus Symbol	Temperature under switching conditions Inverter m Rated Values Item	Со		-40	1	ing 00	Unit
R_{thCH} T_{vjop} $\textbf{Diode, I}$ \textbf{Maximu} $Symbol$ V_{RRM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage	Со		-40	12 40	ing 00	Unit V
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ I_{F} \\ I_{FRM} \\ \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC	Co T _{vj} =25°C		-40	12 40	ing 00 00	Unit V A
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ I_{F} \\ I_{FRM} \\ \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current	T_{vj} =25°C t_p =1ms		-40	12 40	ing 00 00	Unit V A
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ I_{F} \\ I_{FRM} \\ \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current	T_{vj} =25°C T_{vj} =25°C T_{p} =1ms T_{p} =400A	nditions		12 40 80	ing 00 00 00	Unit V A
R_{thCH} T_{vjop} $\textbf{Diode, I}$ \textbf{Maximu} $Symbol$ V_{RRM} I_{F} I_{FRM} $\textbf{Characte}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values	T_{vj} =25°C t_p =1ms	nditions T _{vj} =25°C	-	12 40 80	ing 00 00 00 00	Unit V A A
R_{thCH} T_{vjop} $\textbf{Diode, I}$ \textbf{Maximu} $Symbol$ V_{RRM} I_{F} I_{FRM} $\textbf{Characte}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values	T_{vj} =25°C T_{vj} =25°C T_{p} =1ms T_{p} =400A	nditions T _{vj} =25°C T _{vj} =125°C	- -	12 40 80 1.60 1.35	ing 00 00 00 - -	Unit V A A
R_{thCH} T_{vjop} $\textbf{Diode, I}$ \textbf{Maximu} $Symbol$ V_{RRM} I_{F} I_{FRM} $\textbf{Characte}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values	T_{vj} =25°C T_{vj} =25°C T_{p} =1ms T_{p} =400A	nditions	- -	12 40 80 1.60 1.35 1.30	ing 00 00 00 - - -	Unit V A A
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ I_{F} \\ I_{FRM} \\ \hline \textbf{Characte} \\ V_{F} \\ \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage	T_{vj} =25°C T_{vj} =25°C T_{p} =1ms T_{p} =400A	nditions $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$	- - -	1.60 1.35 1.30 191	ing 00 00 00 - - -	Unit V A A
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ I_{F} \\ I_{FRM} \\ \hline \textbf{Characte} \\ V_{F} \\ \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage	$T_{vj}=25^{\circ}C$ $t_{p}=1 \text{ms}$ $I_{F}=400 \text{A}$ $V_{GE}=0 \text{V}$	nditions	- - - -	1.60 1.35 1.30 191 328	ing 00 00 00	Unit V A A
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ I_{F} \\ I_{FRM} \\ \hline \textbf{Characte} \\ V_{F} \\ \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage	T_{vj} =25°C t_p =1ms I_F =400A V_{GE} =0V	nditions $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	- - - -	1.60 1.35 1.30 191 328 364	ing 00 00 00 - - - -	Unit V A A
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ \hline I_{F} \\ \textbf{Characte} \\ \hline V_{F} \\ \\ \hline I_{RM} \\ \hline \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current	$\begin{array}{c} Co \\ T_{vj} = 25^{\circ}C \\ \\ I_{p} = 1 ms \\ \\ I_{F} = 400 A \\ V_{GE} = 0 V \\ \\ \\ V_{R} = 600 V \\ \\ I_{F} = 400 A \\ \end{array}$	nditions $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$	- - - - -	1.60 1.35 1.30 191 328 364 202	ing 00 00 00 	Unit V A A V
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ \hline I_{F} \\ \textbf{Characte} \\ \hline V_{F} \\ \\ \hline I_{RM} \\ \hline \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current	$\begin{array}{c} Co \\ T_{vj} = 25 ^{\circ} C \\ \\ t_{p} = 1 ms \\ \\ \\ I_{F} = 400 A \\ V_{GE} = 0 V \\ \\ \\ V_{R} = 600 V \\ \\ I_{F} = 400 A \\ \\ di_{F} / dt = -4264 A / \mu s \\ \\ \end{array}$	nditions $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$	- - - - -	1.60 1.35 1.30 191 328 364 202 388	ing 00 00 00 	Unit V A A V
RthCH Tvjop Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F I _{RM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current	$\begin{array}{c} Co \\ T_{vj} = 25^{\circ}C \\ \\ I_{p} = 1 ms \\ \\ I_{F} = 400 A \\ V_{GE} = 0 V \\ \\ \\ V_{R} = 600 V \\ \\ I_{F} = 400 A \\ \end{array}$	nditions $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$	- - - - - -	1.60 1.35 1.30 191 328 364 202 388 547	ing 00 00	Unit V A A V A
$\begin{array}{c} R_{thCH} \\ T_{vjop} \\ \hline \textbf{Diode,} \\ \textbf{Maximu} \\ Symbol \\ V_{RRM} \\ \hline I_{F} \\ \textbf{Characte} \\ \hline V_{F} \\ \\ \hline I_{RM} \\ \hline \end{array}$	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current Reverse recovery time	$\begin{array}{c} Co \\ T_{vj} = 25 ^{\circ} C \\ \\ t_{p} = 1 ms \\ \\ \\ I_{F} = 400 A \\ V_{GE} = 0 V \\ \\ \\ V_{R} = 600 V \\ \\ I_{F} = 400 A \\ \\ di_{F} / dt = -4264 A / \mu s \\ \\ \end{array}$	nditions $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$	- - - - - -	1.60 1.35 1.30 191 328 364 202 388 547 30.1	ing 00 00 00	Unit V A A V
RthCH Tvjop Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F I _{RM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current Reverse recovery time	$\begin{array}{c} Co \\ T_{vj} = 25 ^{\circ} C \\ \\ t_{p} = 1 ms \\ \\ \\ I_{F} = 400 A \\ V_{GE} = 0 V \\ \\ \\ V_{R} = 600 V \\ \\ I_{F} = 400 A \\ \\ di_{F} / dt = -4264 A / \mu s \\ \\ \end{array}$	nditions $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$	- - - - - - -	12 40 80 1.60 1.35 1.30 191 328 364 202 388 547 30.1 82.1	ing 00 00	Unit V A A V A
RthCH Tvjop Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F I _{RM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current Reverse recovery time	$\begin{array}{c} Co \\ T_{vj} = 25 ^{\circ} C \\ \\ t_{p} = 1 ms \\ \\ \\ I_{F} = 400 A \\ V_{GE} = 0 V \\ \\ \\ V_{R} = 600 V \\ \\ I_{F} = 400 A \\ \\ di_{F} / dt = -4264 A / \mu s \\ \\ \end{array}$	nditions $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$	- - - - - - - -	12 40 80 1.60 1.35 1.30 191 328 364 202 388 547 30.1 82.1 101.9	ing 00 00 00	Unit V A A V A

R _{thJC}	Thermal resistance, junction to case	per diode	-	0.11	-	K/W
R_{thCH}	Thermalresistance,case to heatsink	per diode/ λgrease=1W/(m·K)	-		-	K/W
$T_{ m vjop}$	Temperature under switching conditions		-40		150	°C

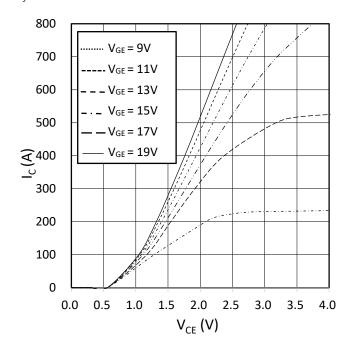
Module

Symbol	Item	Conditions	Rating		Unit	
$V_{\rm ISOL}$	Isolation voltage	Terminals to baseplate, RMS,f=50Hz,t=1min	4000		V	
-	Material of module baseplate	-	Cu		-	
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al ₂ O ₃		-	
T_{stg}	Storage temperature	-	-40~125		°C	
C 1 1	Item	C. Thi		Values		Unit
Symbol		Conditions	Min.	Тур.	Max.	
M	Mounting torque for module mounting	Screw M6	3.0	-	6.0	Nm
	Terminal connection torque	Screw M6	2.5	-	5.0	Nm
ds	Creepage distance	Terminal to terminal	-	23	-	
		Terminal to base plate	-	29	-	mm
da	Clearance	Terminal to terminal	-	11	-	
		Terminal to base plate	-	23	-	mm
m	Weight	-	-	315	-	g

utput characteristic IGBT, Inverter (typical)

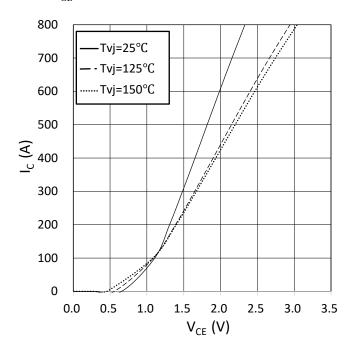
$$I_C = f(V_{CE})$$

 $T_{vj} = 150$ °C



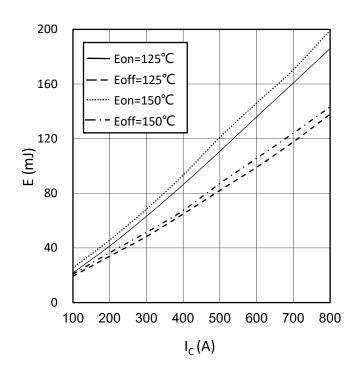
output characteristic IGBT, Inverter (typical)

$$I_{C} = f(V_{CE})$$
$$V_{GE} = 15 \text{ V}$$



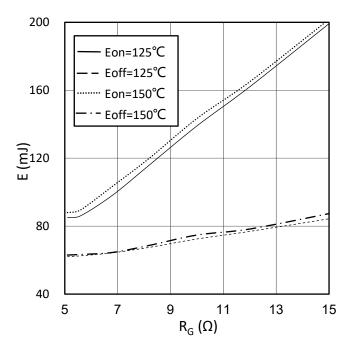
switching losses IGBT,Inverter(typical)

$$\begin{split} E_{on} &= f\left(I_{C}\right), \, E_{off} = f\left(I_{C}\right) \\ V_{GE} &= \pm 15 V, \, R_{Gon} = 5.1 \Omega, \, R_{Goff} = 5.1 \Omega, \, V_{CE} = 600 V \end{split}$$



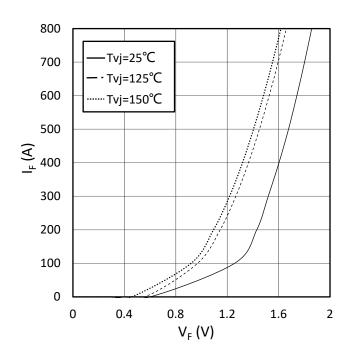
switching losses IGBT,Inverter(typical)

$$\begin{split} E_{on} &= f\left(R_{G}\right), \, E_{off} {=} \, f\left(R_{G}\right) \\ V_{GE} &= \pm 15 V, \, I_{C} = 400 A, \, V_{CE} {=} \, 600 V \end{split}$$



forward characteristic of Diode, Inverter (typical)

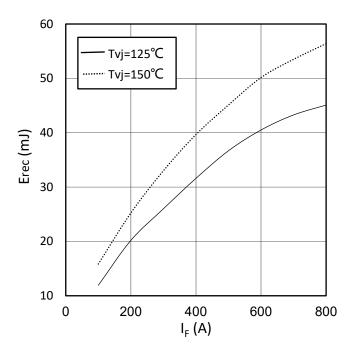
$$I_{F}=f\left(V_{F}\right)$$



switching losses Diode, Inverter (typical)

$$E_{rec} = f\left(I_F\right)$$

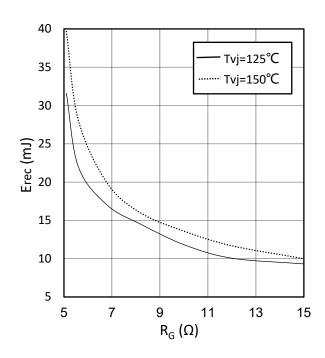
$$R_{Gon} = 5.1\Omega, V_{CE} = 600V$$



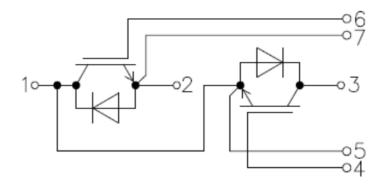
switching losses Diode, Inverter (typical)

$$E_{rec} = f(R_G)$$

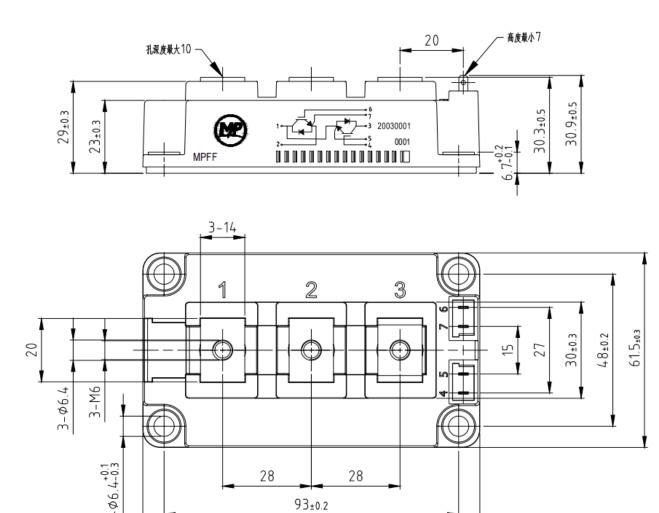
$$I_F = 400A, V_{CE} = 600V$$



Circuit diagram headline



Package outlines (Unit: mm)



106.7_{±0.35}

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